**RED** **Item No.: 102205**

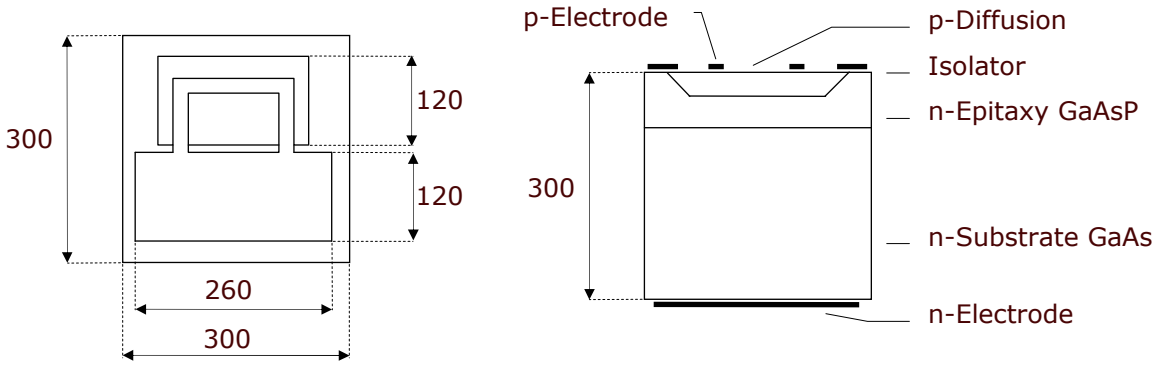
1. This specification applies to GaAsP / GaAs LED Chips

2. Structure

2.1 Planar structure

2.2 Electrodes p-side (anode) Al
n-side (cathode) Au alloy

3. Outlines (dimensions in microns)




4. Electrical and optical characteristics (T=25°C)

| *Parameter* | *Symbol* | *Conditions* | *min* | *typ* | *max* | *Unit* |
|---|---|---|---|---|---|---|
| Forward voltage | $V_F$ | $I_F$ = 10 mA | | 1,65 | 1,84 | V |
| Reverse voltage | $V_R$ | $I_R$ = 10 µA | 5 | | | V |
| Luminous intensity * | $I_V$ | $I_F$ = 10 mA | 250 | 400 | | µcd |
| Peak wavelength | $\lambda_P$ | $I_F$ = 10 mA | | 660 | | nm |

* On request, wafers will be delivered according to luminous intensity classes
Brightness measurement at OSA on gold plate

5. Packing

Dice on adhesive film with wire bond side on top

6. Labeling

| Type | Lot No. | $I_V$ typ<br>min<br>max | Quantity |
|---|---|---|---|

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